



Substitute for form 1449A/PTO  
**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(Use as many sheets as necessary)

Complete if Known	
Application Number	10/781,035
Filing Date	February 18, 2004
First Named Inventor	Eldridge, Jerome
Group Art Unit	2818
Examiner Name	Ho, Tu-Tu

Sheet 1 of 1

Attorney Docket No: 1303.063US2

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	<del>US20010013621</del>	<del>08/01/2001</del>	<del>Nakazato, Kazuo</del>	<del>257</del>	<del>314</del>	<del>12/08/2000</del> duplicate
TH	US-4,449,205	05/15/1984	Hoffman, Charles R.	365	182	02/19/1982
	US-4,495,219	01/22/1985	Kato, Takashi, et al.	427	82	10/08/1982
	US-4,688,078	08/18/1987	Hseih, Ning	257	321	12/11/1985
	US-4,717,943	01/05/1988	Wolf, Hans P., et al.	357	23.5	07/16/1986
	US-4,794,565	12/27/1988	Wu, Albert T., et al.	365	185	09/15/1986
	US-4,870,470	09/26/1989	Bass Jr., Roy S., et al.	357	23.5	10/16/1987
	US-4,939,559	07/03/1990	DiMaria, D. J., et al.	257	38	04/01/1986
	US-5,445,984	08/29/1995	Gary, Hong, et al.	437	43	11/28/1994
	US-5,455,792	10/03/1995	Yi, Yong-Wan	365	185.12	09/09/1994
	US-5,510,278	04/23/1996	Bich-Yen, Nguyen, et al.	437	40	09/06/1994
	US-5,617,351	04/01/1997	Bertin, Claude L., et al.	365	185.05	06/05/1995
	US-5,646,430	07/08/1997	Kaya, Cetin, et al.	257	322	08/28/1995
	US-6,127,227	10/03/2000	Lin, Chrong J., et al.	438	261	01/25/1999
	US-6,169,306	01/02/2001	Gardner, Mark I., et al.	257	310	07/27/1998
	US-6,288,419	09/11/2001	Prall, Kirk D., et al.	257	213	07/09/1999
	US-6,377,070	04/23/2002	Forbes, Leonard	326	41	02/09/2001
	US-6,514,842	02/04/2003	Prall, K. D., et al.	438	593	08/08/2001
TH	US-6,730,575	05/04/2004	Eldridge, Jerome M.	257	310	08/30/2001

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
TH		HAN, KWANGSEOK, "Characteristics of P-Channel Si Nano-Crystal Memory", <u>IEDM Technical Digest, International Electron Devices Meeting</u> , (December 10-13, 2000), 309-312	
		INUMIYA, S., et al., "Conformable formation of high quality ultra-thin amorphous Ta2 O5 gate dielectrics utilizing water assisted deposition (WAD) for sub 50 nm damascene metal gate MOSFETs", <u>IEDM Technical Digest, International Electron Devices Meeting</u> , (December 10-13, 2000), 649-652	
		MANCHANDA, L., "Si-doped aluminates for high temperature metal-gate CMOS: Zr-Al-Si-O, a novel gate dielectric for low power applications", <u>IEDM Technical Digest, International Electron Devices Meeting</u> , (December 10-13, 2000), 23-26	
TH		YAMAGUCHI, TAKESHI, "Band Diagram and Carrier Conduction Mechanism in ZrO2/Zr-silicate/Si MIS Structure Fabricated by Pulsed-laser-ablation Deposition", <u>Electron Devices Meeting, 2000. IEDM Technical Digest, International</u> , (2000), 19-22	

EXAMINER

TH TH +10

DATE CONSIDERED

Oct 2004